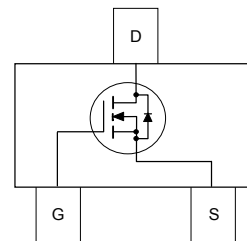
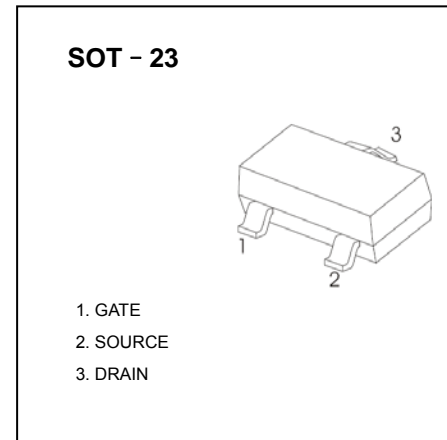


**Applications**

- Load switch
- Battery protection
- Power management

**Features**

- $V_{DS} (V) = 20V$
- $R_{DS(ON)} < 45m \Omega (V_{GS} = 4.5V)$
- $R_{DS(ON)} < 60m \Omega (V_{GS} = 2.5V)$



**Absolute Maximum Ratings**  $T_A=25^\circ C$  unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain-Source Voltage	20	V
$V_{GSS}$	Gate-Source Voltage	$\pm 12$	V
$I_D$	Drain Current – Continuous – Pulsed	0.9	A
		2	
$P_D$	Maximum Power Dissipation	0.35	W
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ C$
<b>Thermal Characteristics</b>			
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	357	$^\circ C/W$

**Electrical Characteristics**
 $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain–Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		15		$\text{mV}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 16\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSSF}$	Gate–Body Leakage, Forward	$V_{GS} = 12\text{ V}, V_{DS} = 0\text{ V}$			100	nA
$I_{GSSR}$	Gate–Body Leakage, Reverse	$V_{GS} = -12\text{ V}, V_{DS} = 0\text{ V}$			-100	nA
<b>On Characteristics (Note 2)</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	0.6	1	1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		-3		$\text{mV}/^\circ\text{C}$
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = 4.5\text{ V}, I_D = 0.9\text{ A}$ $V_{GS} = 2.5\text{ V}, I_D = 0.7\text{ A}$			45 60	$\text{m}\Omega$
$I_{D(on)}$	On–State Drain Current	$V_{GS} = 4.5\text{ V}, V_{DS} = 5\text{ V}$	1			A
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{ V}, I_D = 0.9\text{ A}$		3		S
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$		109		pF
$C_{oss}$	Output Capacitance			30		pF
$C_{rfs}$	Reverse Transfer Capacitance			14		pF
<b>Switching Characteristics (Note 2)</b>						
$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = 10\text{ V}, I_D = 1\text{ A}, V_{GS} = 4.5\text{ V}, R_{GEN} = 6\ \Omega$		4.5	9	ns
$t_r$	Turn–On Rise Time			7	14	ns
$t_{d(off)}$	Turn–Off Delay Time			8	16	ns
$t_f$	Turn–Off Fall Time			1.4	2.8	ns
$Q_g$	Total Gate Charge	$V_{DS} = 10\text{ V}, I_D = 0.9\text{ A}, V_{GS} = 4.5\text{ V}$		1.1	1.5	nC
$Q_{gs}$	Gate–Source Charge			0.26		nC
$Q_{gd}$	Gate–Drain Charge			0.26		nC
<b>Drain–Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain–Source Diode Forward Current				0.29	A
$V_{SD}$	Drain–Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 0.29\text{ A}$		0.75	1.2	V
$t_{rr}$	Diode Reverse Recovery Time	$I_F = 0.9\text{ A}, dI_F/dt = 100\text{ A}/\mu\text{s}$		7.4		nS
$Q_{rr}$	Diode Reverse Recovery Charge			2.2		nC

**Notes:**

1. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

Typical Characteristics

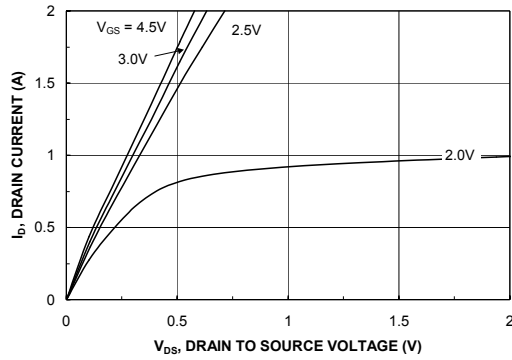


Figure 1. On-Region Characteristics.

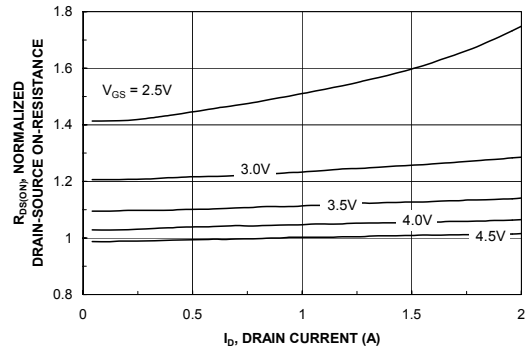


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

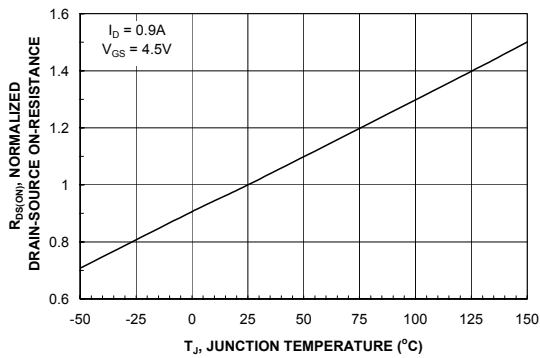


Figure 3. On-Resistance Variation with Temperature.

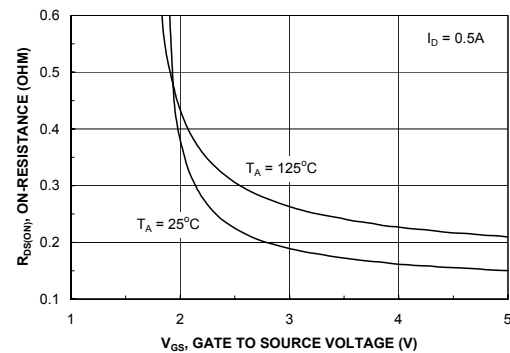


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

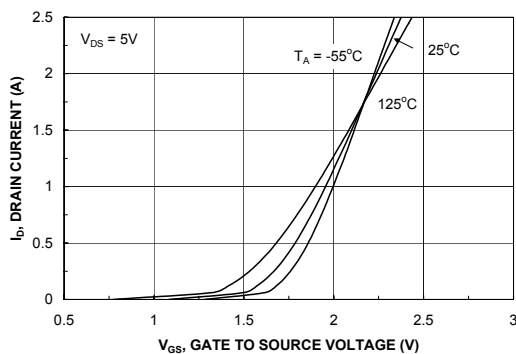


Figure 5. Transfer Characteristics.

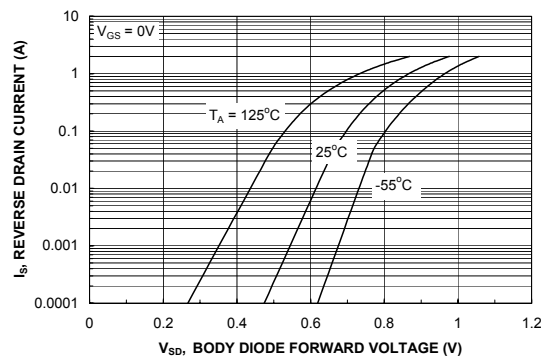


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

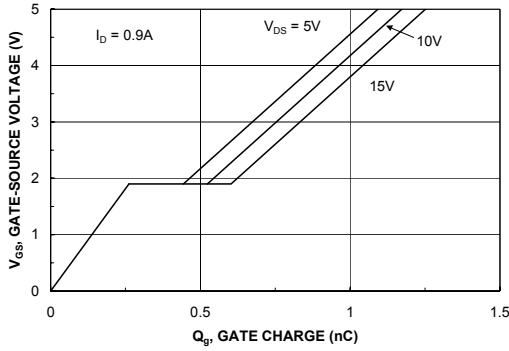


Figure 7. Gate Charge Characteristics.

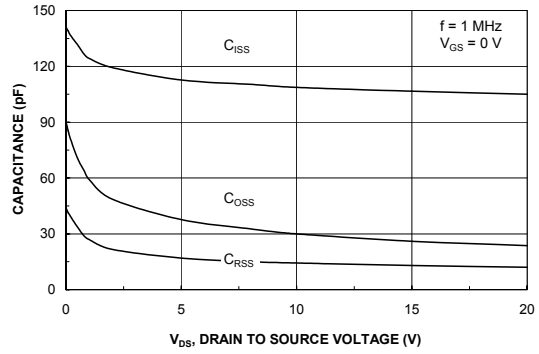


Figure 8. Capacitance Characteristics.

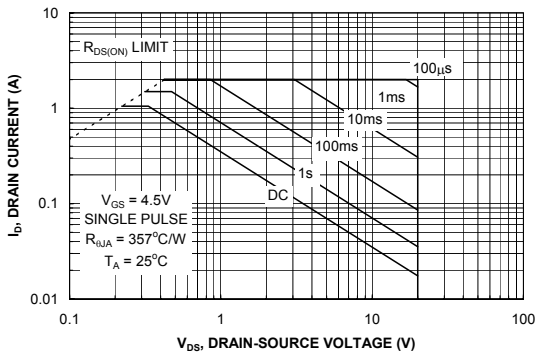


Figure 9. Maximum Safe Operating Area.

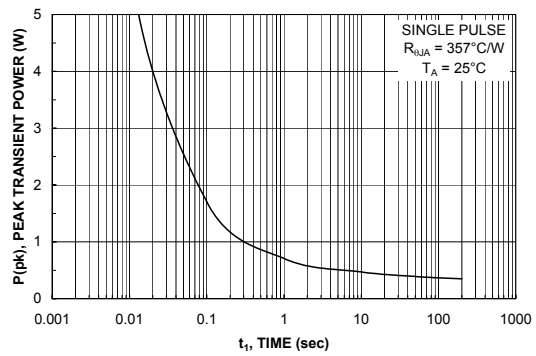


Figure 10. Single Pulse Maximum Power Dissipation.

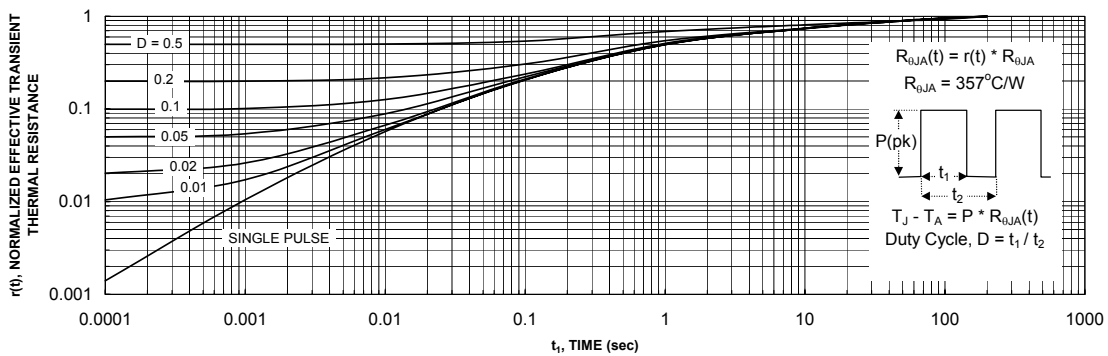
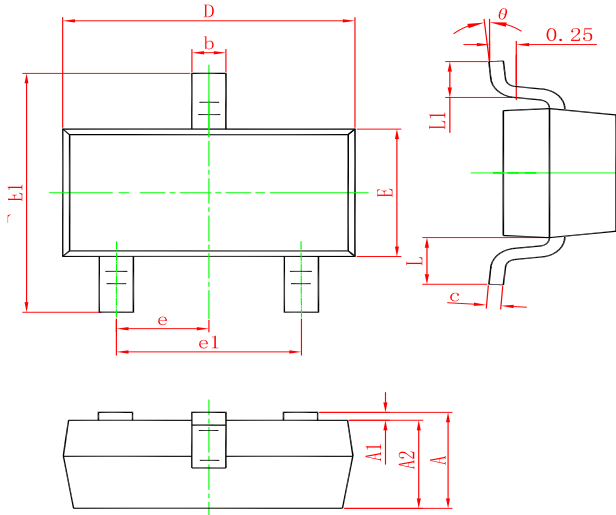


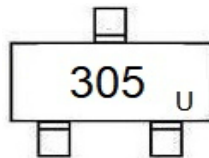
Figure 11. Transient Thermal Response Curve.

**SOT-23 PACKAGE OUTLINE DIMENSIONS**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

**Marking**



**Ordering information**

Order code	Package	Baseqty	Deliverymode
UMW FDV305N	SOT-23	3000	Tape and reel

单击下面可查看定价，库存，交付和生命周期等信息

[>>UMW\(友台半导体\)](#)